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DMN3061SW

N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV_{DSS}	$R_{DS(ON)}$ Max	I_D Max T_A = +25°C
30V	60mΩ @ V_{GS} = 10V	2.7A
	100mΩ @ V_{GS} = 4.5V	2.1A

Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative. https://www.diodes.com/quality/product-definitions/**

Description and Applications

This MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$) yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

- General Purpose Interfacing Switch
- Power Management Functions
- DC-DC Converters
- Analog Switch

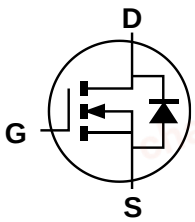
Mechanical Data

- Case: SOT323
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish—Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 e3
- Weight: 0.027 grams (Approximate)

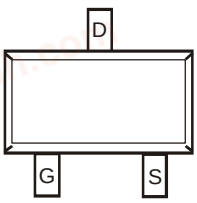
SOT323



Top View



Equivalent Circuit



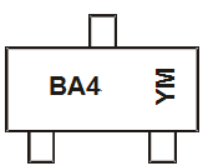
Top View

Ordering Information (Note 4)

Part Number	Case	Packaging
DMN3061SW-7	SOT323	3,000/Tape & Reel
DMN3061SW-13	SOT323	10,000/Tape & Reel

Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



BA4 = Product Type Marking Code
YM or $\overline{Y}$M= Date Code Marking
Y or $\overline{Y}$= Year (ex: H = 2020)
M = Month (ex: 9 = September)

Date Code Key

Year	2019	2020	2021	2022	2023	2024	2025	2026	2027	2028	2029	2030
Code	G	H	I	J	K	L	M	N	O	P	R	S

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

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Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	30	V
Gate-Source Voltage			V_{GSS}	±20	V
Continuous Drain Current (Note 6) V_{GS} = 10V	Steady State	T_A = +25°C T_A = +70°C	I_D	2.7 2.2	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I_{DM}	22	A
Maximum Body Diode Forward Current (Note 5)			I_S	0.67	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)		P_D	0.49	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\Theta JA}$	254	°C/W
Total Power Dissipation (Note 6)		P_D	0.65	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\Theta JA}$	191	°C/W
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	30	—	—	V	V_{GS} = 0V, I_D = 250µA
Zero Gate Voltage Drain Current @T_C = +25°C	I_{DSS}	—	—	1.0	µA	V_{DS} = 24V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	±100	nA	V_{GS} = ±20V, V_{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(TH)}$	0.5	—	1.8	V	V_{DS} = V_{GS}, I_D = 250µA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	41	60	mΩ	V_{GS} = 10V, I_D = 3.1A
		—	48	100		V_{GS} = 4.5V, I_D = 2A
		—	56	200		V_{GS} = 3.3V, I_D = 1.5A
Diode Forward Voltage	V_{SD}	—	0.7	1	V	V_{GS} = 0V, I_S = 1A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C_{iss}	—	278	—	pF	V_{DS} = 15V, V_{GS} = 0V, f = 1.0MHz
Output Capacitance	C_{oss}	—	44	—	pF	
Reverse Transfer Capacitance	C_{rss}	—	29	—	pF	
Gate Resistance	R_g	—	4.2	—	Ω	V_{DS} = 0V, V_{GS} = 0V, f = 1MHz
Total Gate Charge	Q_g	—	3.5	—	nC	V_{DS} = 15V, V_{GS} = 4.5V, I_D = 3A
Gate-Source Charge	Q_{gs}	—	0.1	—	nC	
Gate-Drain Charge	Q_{gd}	—	1.3	—	nC	
Turn-On Delay Time	$t_{D(ON)}$	—	5.7	—	ns	V_{GS} = 10V, V_{DS} = 15V, R_G = 3Ω, R_L = 1.7Ω
Turn-On Rise Time	t_R	—	97	—	ns	
Turn-Off Delay Time	$t_{D(OFF)}$	—	12.6	—	ns	
Turn-Off Fall Time	t_F	—	51	—	ns	

Notes:
5. Device mounted on FR-4 substrate PC board, with minimum recommended pad layout.
6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
7. Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to product testing.

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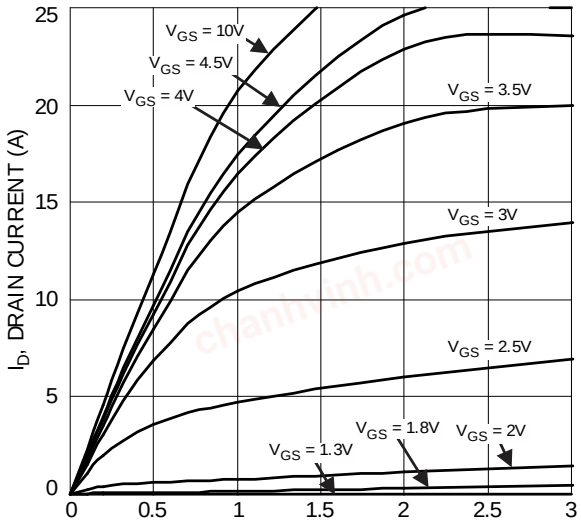


Figure 1 Typical Output Characteristic

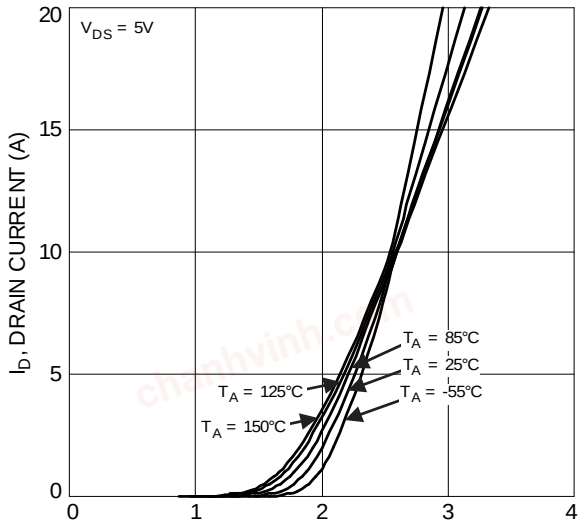


Figure 2 Typical Transfer Characteristics

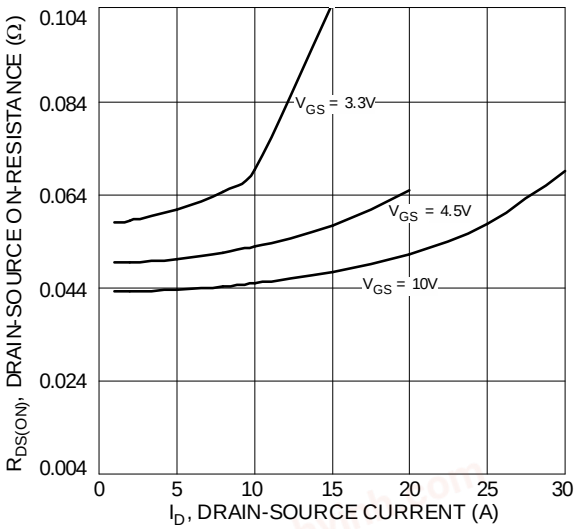


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

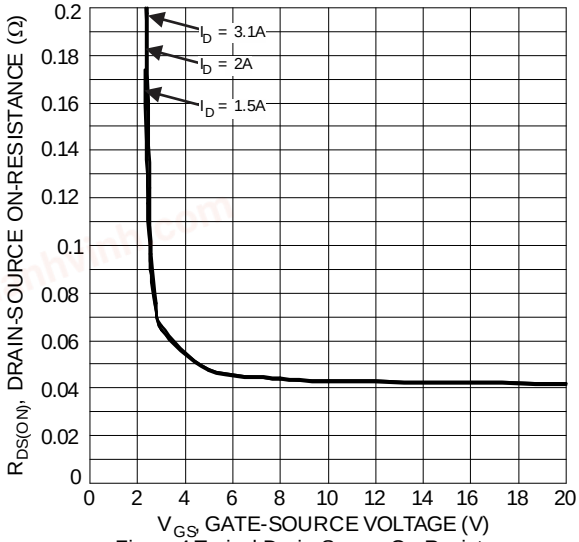


Figure 4 Typical Drain-Source On-Resistance vs. Gate-Source Voltage

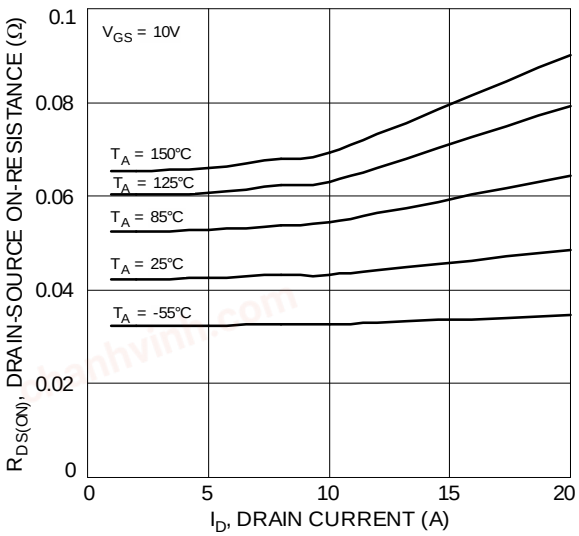


Figure 5 Typical On-Resistance vs. Drain Current and Temperature

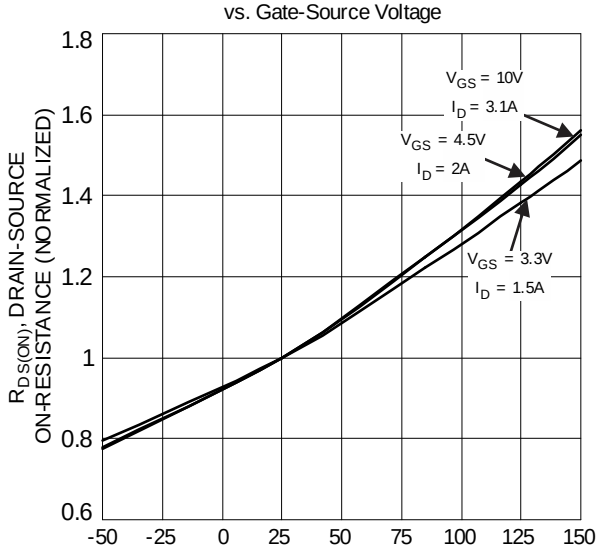


Figure 6 On-Resistance Variation with Temperature

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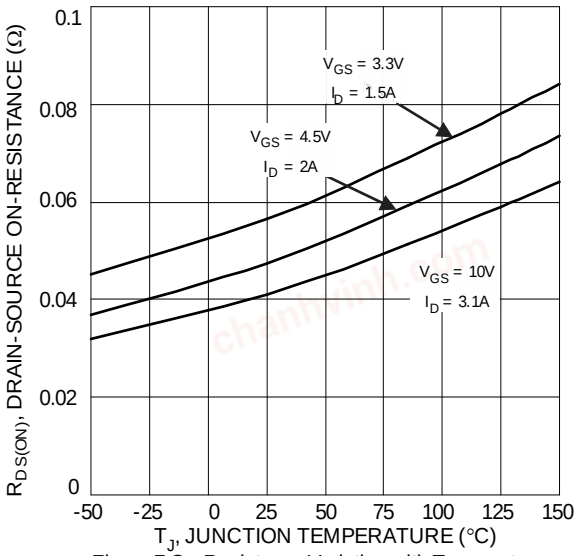


Figure 7 On-Resistance Variation with Temperature

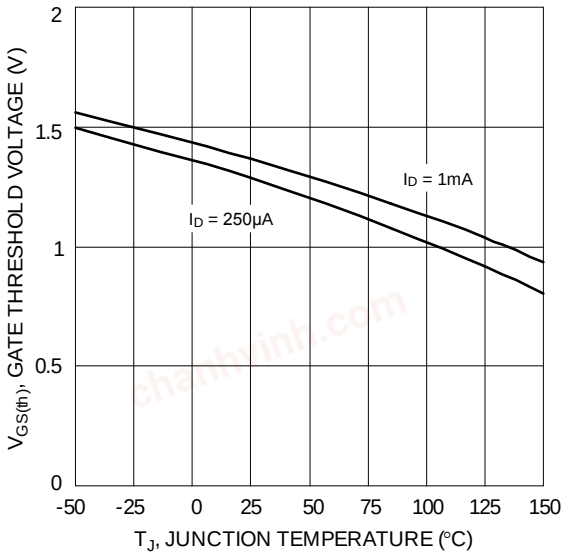


Figure 8 Gate Threshold Variation vs. Junction Temperature

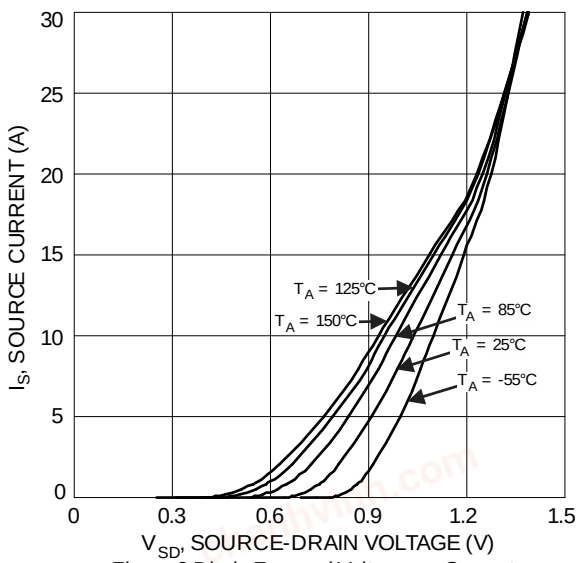


Figure 9 Diode Forward Voltage vs. Current

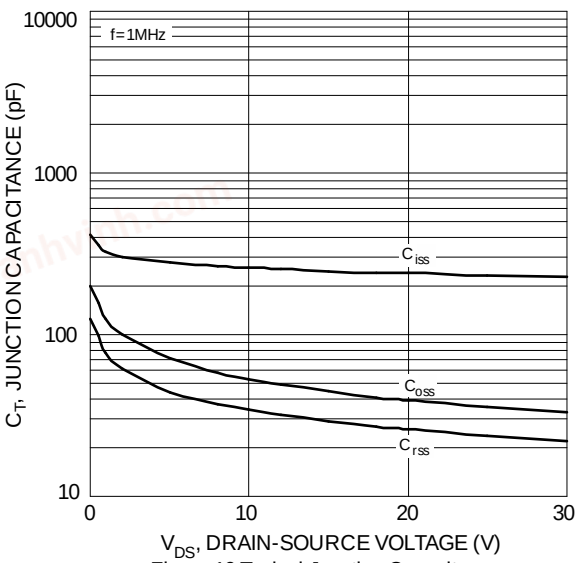


Figure 10 Typical Junction Capacitance

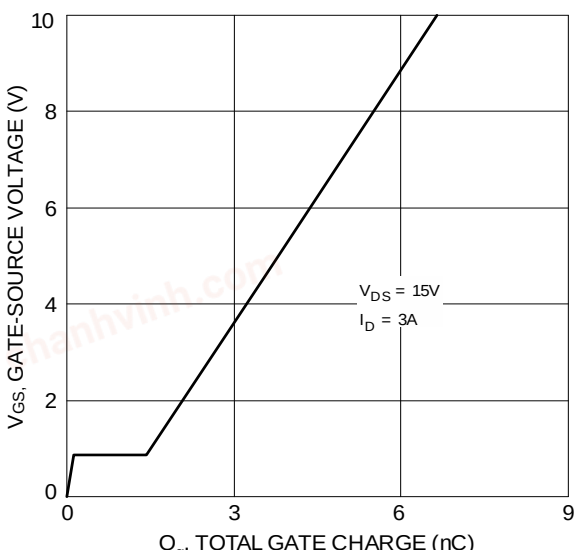


Figure 11 Gate Charge

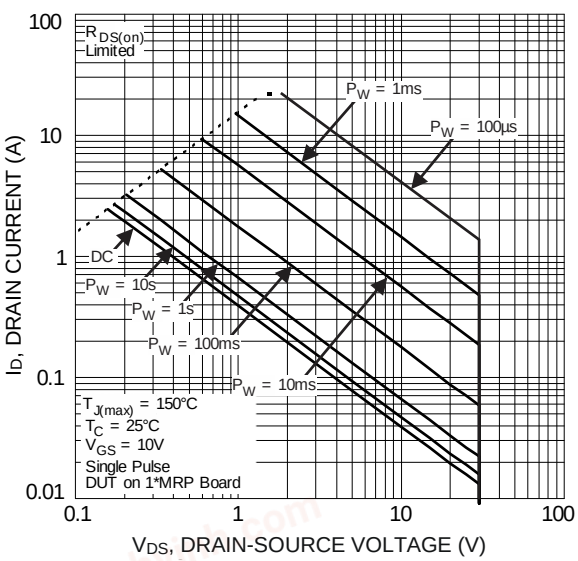


Figure 12 SOA, Safe Operation Area

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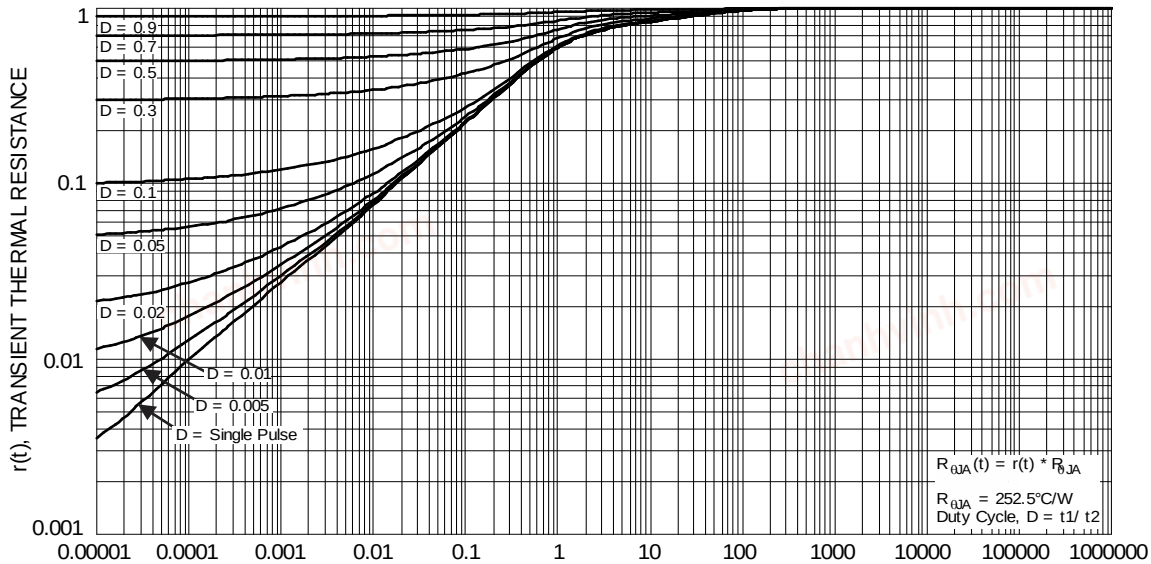


Figure 13 Transient Thermal Resistance

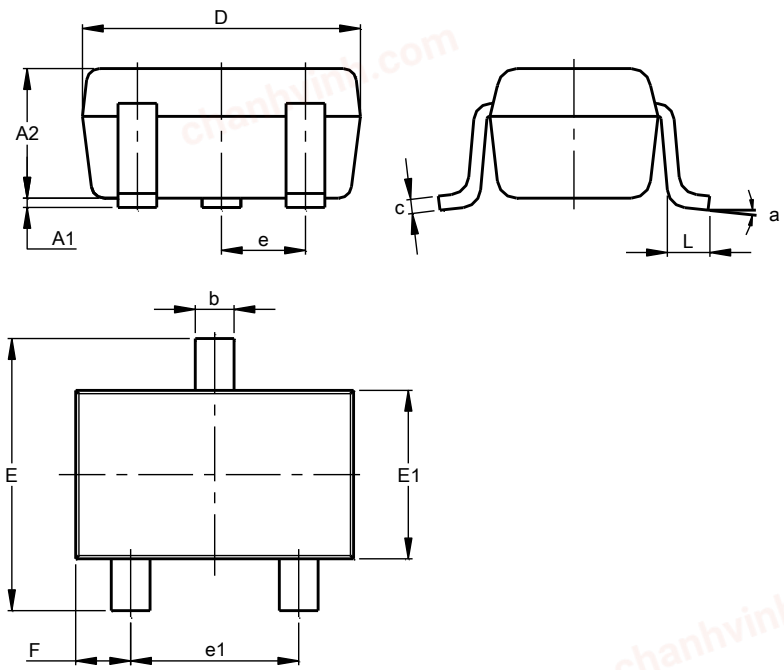
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Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT323

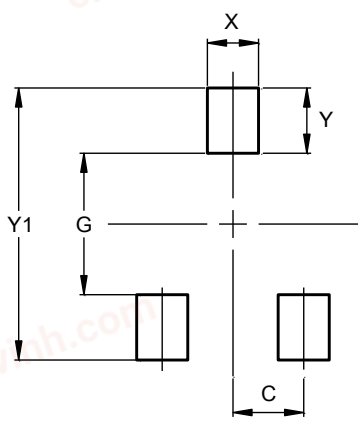


SOT323			
Dim	**Min**	**Max**	**Typ**
A1	0.00	0.10	0.05
A2	0.90	1.00	0.95
b	0.25	0.40	0.30
c	0.10	0.18	0.11
D	1.80	2.20	2.15
E	2.00	2.20	2.10
E1	1.15	1.35	1.30
e	0.650 BSC		
e1	1.20	1.40	1.30
F	0.375	0.475	0.425
L	0.25	0.40	0.30
a	0°	8°	--
All Dimensions in mm			

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT323



Dimensions	Value (in mm)
C	0.650
G	1.300
X	0.470
Y	0.600
Y1	2.500

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